An X-band Schottky diode mixer in SiGe technology with tunable Marchand balun

In this paper, we propose a double balanced mixer with a tunable Marchand balun. The circuit is designed in a SiGe BiCMOS process using Schottky diodes. The tunability of the Marchand balun is used to enhance critical parameters for double balanced mixers. The local oscillator-IF isolation can be changed from –51 to –60.5 dB by tuning. Similarly, the IIP2 can be improved from 41.3 to 48.7 dBm at 11 GHz, while the input referred 1-dB compression point is kept constant at 8 dBm. The tuning have no influence on conversion loss, which remains at 8.8 dB at a LO power level of 11 dBm at the center frequency of 11 GHz. The mixer has a 3 dB bandwidth from 8 to 13 GHz, covering the entire X-band. The full mixer has a size of 2050 μm × 1000 μm.